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## Contact us

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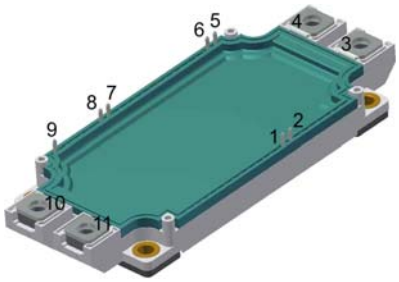
# XPT IGBT Module

$V_{CES}$ = 2x 1200 V
$I_{C25}$ = 465 A
$V_{CE(sat)}$ = 1.8 V

## Phase leg + free wheeling Diodes + NTC

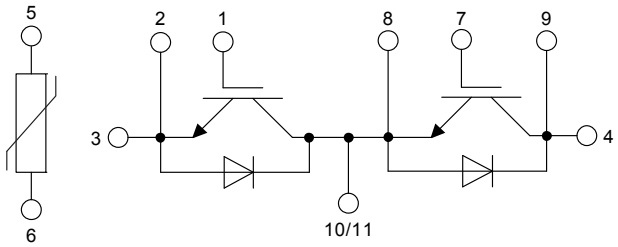
**Part number**

MIXA300PF1200TSF




Backside: isolated

E72873




**Features / Advantages:**

- High level of integration - only one power semiconductor module required for the whole drive
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10 µsec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 3x Ic
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)
- Temperature sense included
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

**Applications:**

- AC motor drives
- Pumps, Fans
- Air-conditioning system
- Inverter and power supplies
- UPS

**Package:** SimBus F

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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| IGBT | | | | Ratings | | | |
|---|---|---|---|---|---|---|---|
| Symbol | Definition | Conditions | | min. | typ. | max. | Unit |
| $V_{CES}$ | *collector emitter voltage* | | $T_{VJ}$ = 25°C | | | 1200 | V |
| $V_{GES}$ | *max. DC gate voltage* | | | | | ±20 | V |
| $V_{GEM}$ | *max. transient gate emitter voltage* | | | | | ±30 | V |
| $I_{C25}$ | *collector current* | | $T_C$ = 25°C | | | 465 | A |
| $I_{C80}$ | | | $T_C$ = 80°C | | | 325 | A |
| $P_{tot}$ | *total power dissipation* | | $T_C$ = 25°C | | | 1500 | W |
| $V_{CE(sat)}$ | *collector emitter saturation voltage* | $I_C$ = 300A; $V_{GE}$ = 15 V | $T_{VJ}$ = 25°C | | 1.8 | 2.1 | V |
| | | | $T_{VJ}$ = 125°C | | 2.15 | | V |
| $V_{GE(th)}$ | *gate emitter threshold voltage* | $I_C$ = 12mA; $V_{GE}$ = $V_{CE}$ | $T_{VJ}$ = 25°C | 5.4 | 5.9 | 6.5 | V |
| $I_{CES}$ | *collector emitter leakage current* | $V_{CE}$ = $V_{CES}$; $V_{GE}$ = 0 V | $T_{VJ}$ = 25°C | | | 0.3 | mA |
| | | | $T_{VJ}$ = 125°C | | 0.3 | | mA |
| $I_{GES}$ | *gate emitter leakage current* | $V_{GE}$ = ±20 V | | | | 1.5 | µA |
| $Q_{G(on)}$ | *total gate charge* | $V_{CE}$ = 600 V; $V_{GE}$ = 15 V; $I_C$ = 300 A | | | 885 | | nC |
| $t_{d(on)}$ | *turn-on delay time* | | | | 110 | | ns |
| $t_r$ | *current rise time* | | | | 68 | | ns |
| $t_{d(off)}$ | *turn-off delay time* | inductive load | $T_{VJ}$ = 125°C | | 290 | | ns |
| $t_f$ | *current fall time* | $V_{CE}$ = 600 V; $I_C$ = 300 A | | | 345 | | ns |
| $E_{on}$ | *turn-on energy per pulse* | $V_{GE}$ = ±15 V; $R_G$ = 2.2 Ω | | | 20 | | mJ |
| $E_{off}$ | *turn-off energy per pulse* | | | | 42 | | mJ |
| RBSOA | *reverse bias safe operating area* | $V_{GE}$ = ±15 V; $R_G$ = 2.2 Ω | $T_{VJ}$ = 125°C | | | | |
| $I_{CM}$ | | $V_{CEmax}$ = 1200 V | | | | 650 | A |
| SCSOA | *short circuit safe operating area* | $V_{CEmax}$ = 1200 V | | | | | |
| $t_{SC}$ | *short circuit duration* | $V_{CE}$ = 900 V; $V_{GE}$ = ±15 V | $T_{VJ}$ = 125°C | | | 10 | µs |
| $I_{SC}$ | *short circuit current* | $R_G$ = 2.2 Ω; non-repetitive | | | tbd | | A |
| $R_{thJC}$ | *thermal resistance junction to case* | | | | | 0.085 | K/W |
| $R_{thCH}$ | *thermal resistance case to heatsink* | | | | 0.04 | | K/W |

| Diode | | | | | | | |
|---|---|---|---|---|---|---|---|
| $V_{RRM}$ | *max. repetitive reverse voltage* | | $T_{VJ}$ = 25°C | | | 1200 | V |
| $I_{F25}$ | *forward current* | | $T_C$ = 25°C | | | 265 | A |
| $I_{F80}$ | | | $T_C$ = 80°C | | | 185 | A |
| $V_F$ | *forward voltage* | $I_F$ = 300A | $T_{VJ}$ = 25°C | | | 2.20 | V |
| | | | $T_{VJ}$ = 125°C | | 1.90 | | V |
| $I_R$ | *reverse current* | $V_R$ = $V_{RRM}$ | $T_{VJ}$ = 25°C | | | * | mA |
| | * not applicable, see Ices value above | | $T_{VJ}$ = 125°C | | * | | mA |
| $Q_{rr}$ | *reverse recovery charge* | | | | 38 | | µC |
| $I_{RM}$ | *max. reverse recovery current* | $V_R$ = 600 V | | | 300 | | A |
| $t_{rr}$ | *reverse recovery time* | -$di_F$/dt = 4500 A/µs | $T_{VJ}$ = 125°C | | 350 | | ns |
| $E_{rec}$ | *reverse recovery energy* | $I_F$ = 300A; $V_{GE}$ = 0 V | | | 15 | | mJ |
| $R_{thJC}$ | *thermal resistance junction to case* | | | | | 0.145 | K/W |
| $R_{thCH}$ | *thermal resistance case to heatsink* | | | | 0.05 | | K/W |

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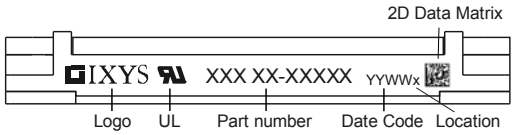
| Package SimBus F | | | | Ratings | | | |
|---|---|---|---|---|---|---|---|
| Symbol | Definition | Conditions | | min. | typ. | max. | Unit |
| $I_{RMS}$ | *RMS current* | per terminal | | | | | A |
| $T_{stg}$ | *storage temperature* | | | -40 | | 125 | °C |
| $T_{VJ}$ | *virtual junction temperature* | | | -40 | | 150 | °C |
| Weight | | | | | 350 | | g |
| $M_D$ | *mounting torque* | | | 3 | | 6 | Nm |
| $M_T$ | *terminal torque* | | | 3 | | 6 | Nm |
| $d_{Spp/App}$ | *creepage distance on surface \| striking distance through air* | | *terminal to terminal* | 12.7 | | | mm |
| $d_{Spb/Apb}$ | | | *terminal to backside* | 10.0 | | | mm |
| $V_{ISOL}$ | *isolation voltage* | t = 1 second | 50/60 Hz, RMS; $I_{ISOL}$ ≤ 1 mA | 3000 | | | V |
| | | t = 1 minute | | 2500 | | | V |
| $R_{pin-chip}$ | *resistance pin to chip* | $V = V_{CEsat} + 2 \cdot R \cdot I_C$ resp. $V = V_F + 2 \cdot R \cdot I_F$ | | | 0.65 | | mΩ |



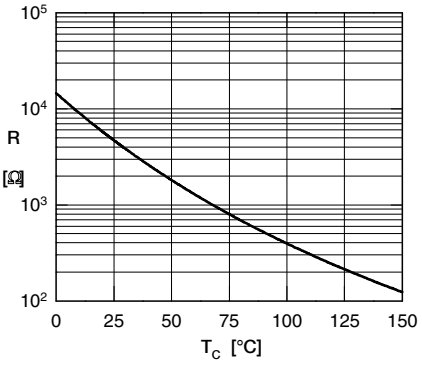

**Part number**

M = Module
I = IGBT
X = XPT IGBT
A = Gen 1 / std
300 = Current Rating [A]
PF = Phase leg + free wheeling Diodes
1200 = Reverse Voltage [V]
T = Thermistor \ Temperature sensor
SF = SimBus F

| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|---|---|---|---|---|---|
| Standard | MIXA300PF1200TSF | MIXA300PF1200TSF | Box | 3 | 512264 |

## Temperature Sensor NTC

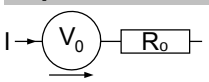
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
|---|---|---|---|---|---|---|
| $R_{25}$ | *resistance* | $T_{VJ}$ = 25° | 4.75 | 5 | 5.25 | kΩ |
| $B_{25/50}$ | *temperature coefficient* | | | 3375 | | K |




Typ. NTC resistance vs. temperature

## Equivalent Circuits for Simulation

** on die level* $T_{VJ}$ = 150 °C




| | | IGBT | Diode | |
|---|---|---|---|---|
| $V_{0\,max}$ | *threshold voltage* | 1.1 | 1.25 | V |
| $R_{0\,max}$ | *slope resistance ** | 4.6 | 8.5 | mΩ |

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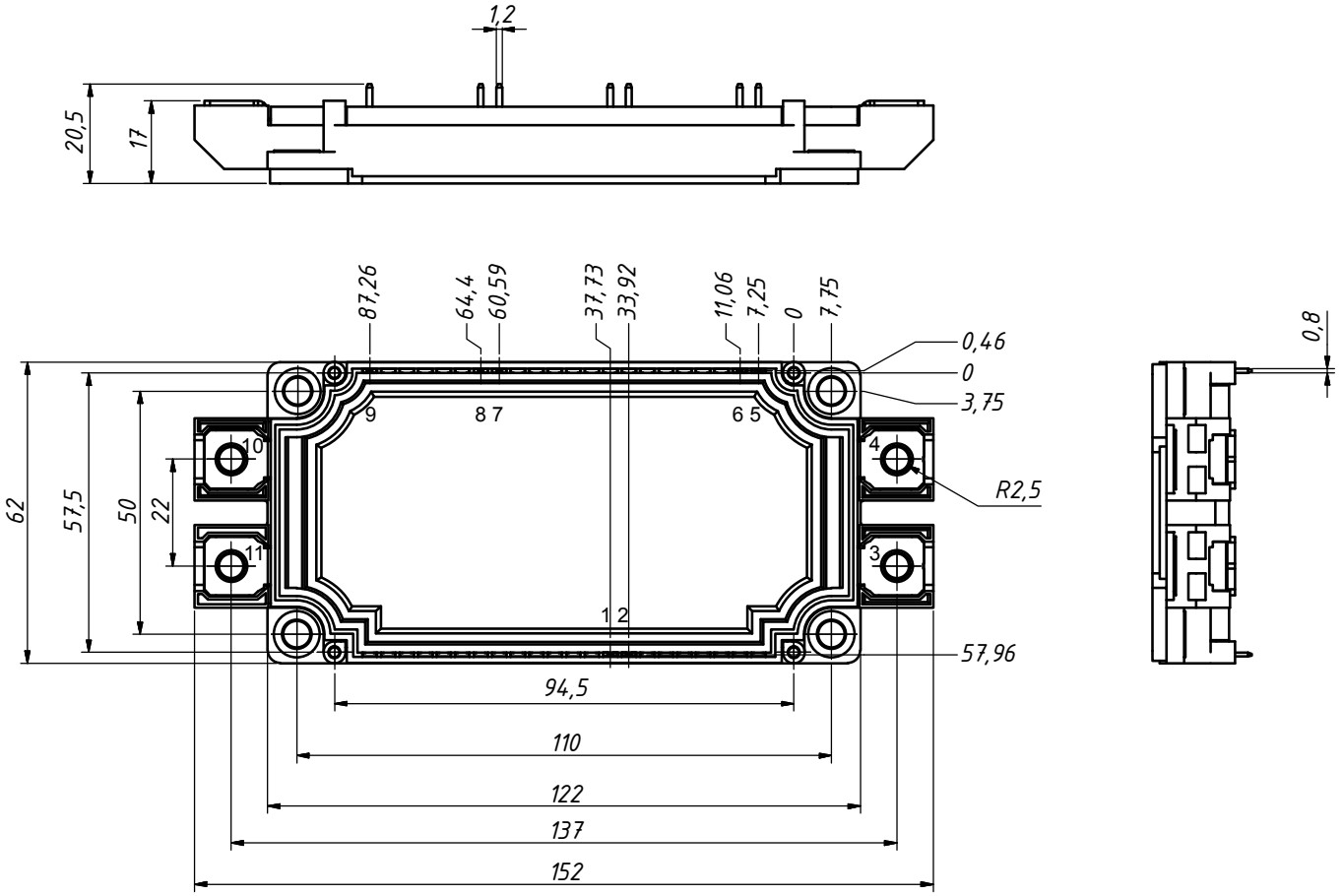
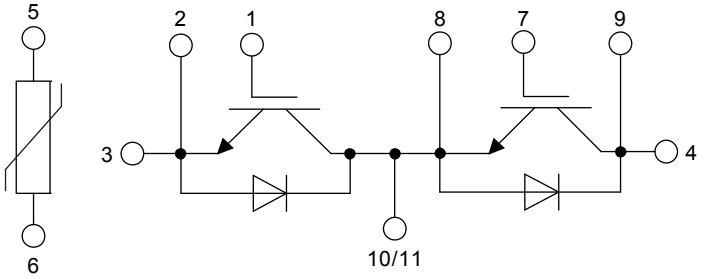
## Outlines SimBus F



## IGBT

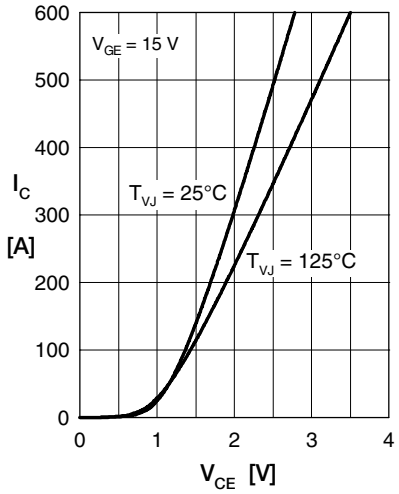



Fig. 1 Typ. output characteristics

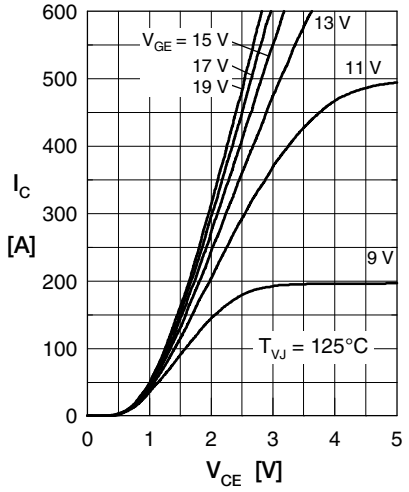



Fig. 2 Typ. output characteristics

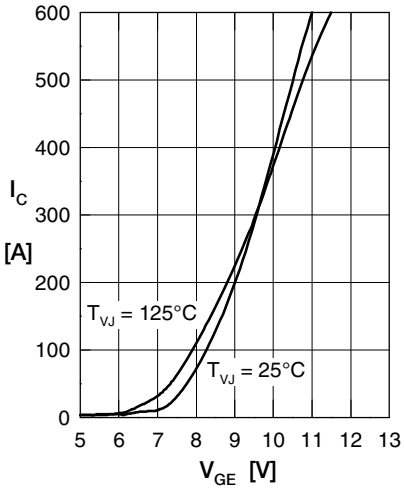



Fig. 3 Typ. transfer characteristics

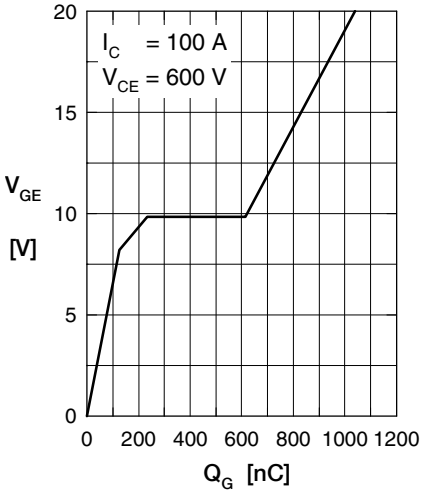



Fig. 4 Typ. turn-on gate charge

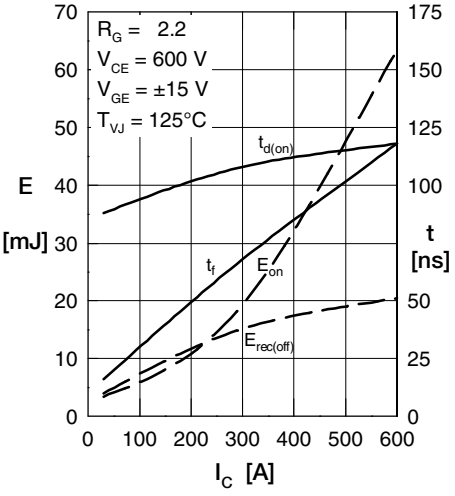



Fig. 5 Typ. turn-on energy & switching times vs. collector current, inductive switching

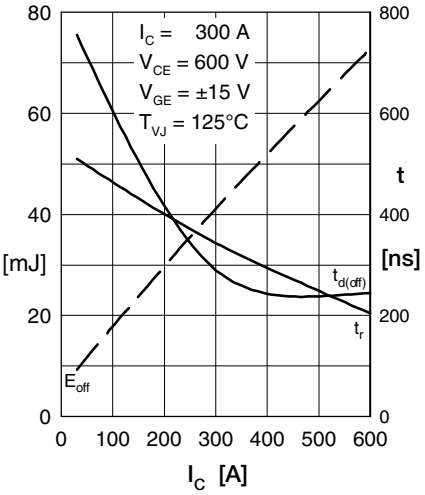



Fig. 6 Typ. switching energy versus gate resistance

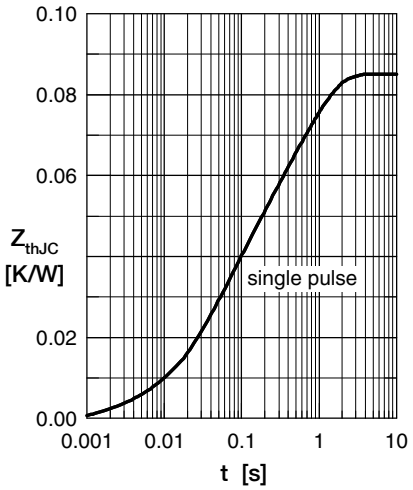



Fig. 7 Typ. trans. therm. impedance

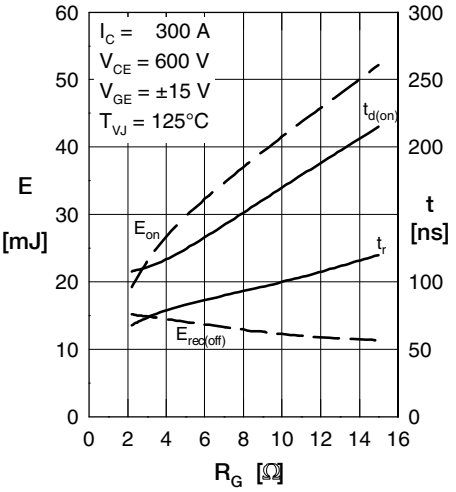



Fig. 8 Typ. turn-on energy, switching times vs. gate resistor, inductive switching

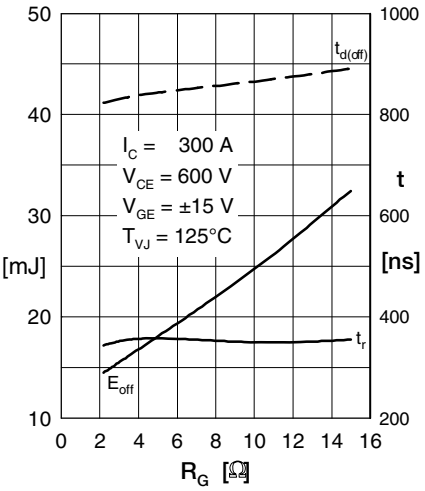



Fig.9 Typ. turn-off energy, switching times vs. gate resistor, inductive switching

## Diode

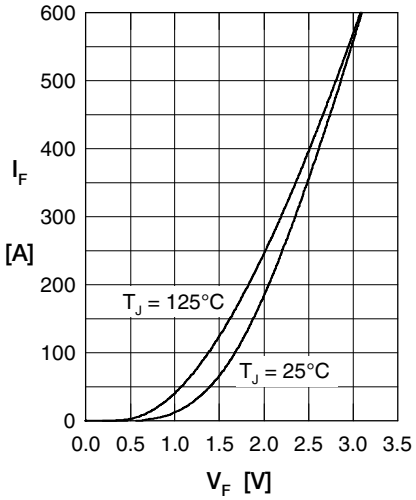



Fig. 1 Typ. Forward current versus $V_F$

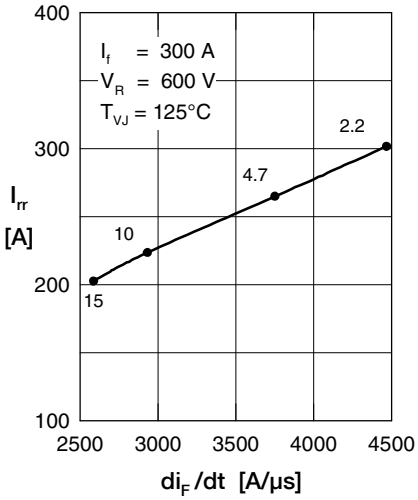



Fig. 2 Typ. reverse recovery characteristics

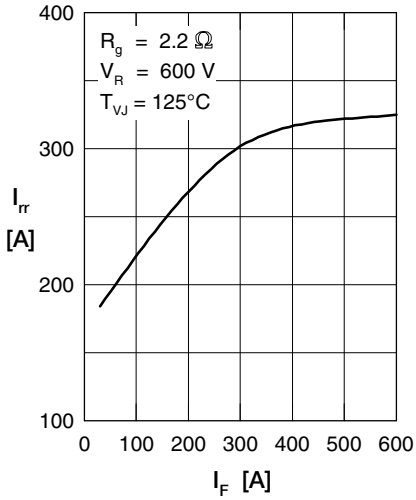



Fig. 3 Typ. reverse recovery characteristics

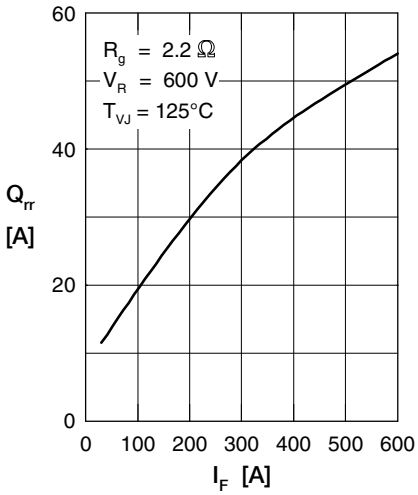



Fig. 4 Typ. reverse recovery characteristics

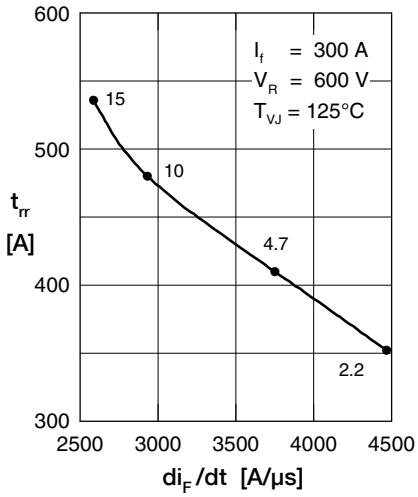



Fig. 5 Typ. recovery time $t_{rr}$ versus $-di_F/dt$

Fig. 6 Typ. recovery energy $E_{rec}$ versus -di/dt

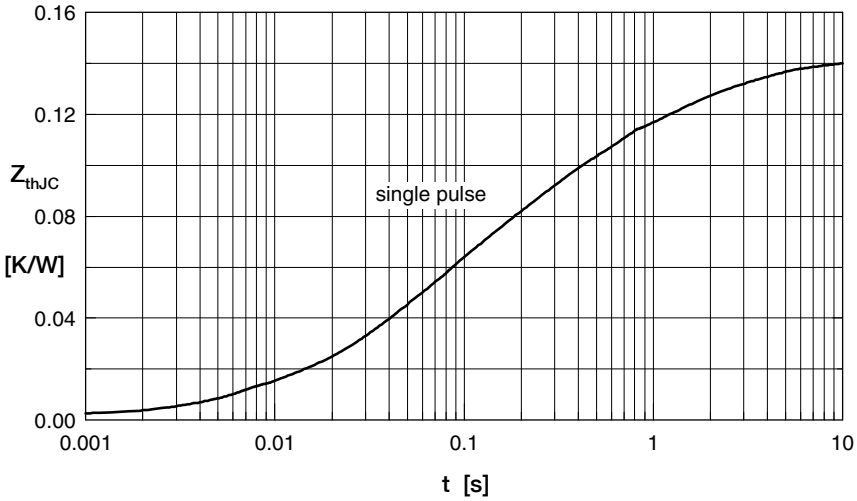



Fig. 7 Typ. transient thermal impedance junction to case